



FIG. 1 is a cross-sectional view of a semiconductor device 1. The device includes a substrate 109 with a top layer 103 and a bottom layer 107b. A central region 3 contains a patterned layer 105b with openings 7a and 7b. A side surface 1 is shown with a roughening process indicated by a dashed line. A dashed line 15 indicates a cross-section through the device. Other labels include 11, 21, 107a, 111, 430, and 413.

Figure 1 is a schematic diagram of a display panel. It shows a rectangular area with a grid of vertical and horizontal bars. The vertical bars are labeled 430, and the horizontal bars are labeled 413. The area is surrounded by a dotted pattern, and the entire structure is labeled 3.